

Metal atomic layer deposition system

System Introduction

The metal atomic layer deposition system deposits films with metal constant. By changing the precursor, it is possible to deposit different films. Currently, this system is available for TiN film deposition, with a thickness between 20~100Å.

- ❖ Full name: Metal atomic layer deposition system
- ❖ Location: class 10000
- ❖ Engineer: Mr. Wen-Cheng Chiu
- ❖ ICE number: (O) 03-57773693 ext. 7569
- ❖ Substitute engineer: Mr. Wen-Cheng Chiu
- ❖ ICE number: (O) 03-57773693 ext. 7569
- ❖ Chemicals used on machine:
 - (1) Bulk gases: **NH₃, H₂, N₂, Ar, O₂**
 - (2) Specialty gases:
 - (3) Bottled chemicals: Metal-organic compounds,
- ❖ Process mode or reaction chamber: Thermal mode
- ❖ Reaction chamber vacuum range: 5e-2 torr
- ❖ Vacuum pump: Turbo pump
- ❖ Substances in exhaust emissions: C, N, O
- ❖ Separate local scrubber: Provided by facility
- ❖ Reaction chamber temperature range: 450°C
- ❖ Type of cooling system: Cooling water supplied by facility
- ❖ Other special hazards: Organic compounds, gases, etc.
- ❖ Manufacturer/agent: NEW YF PRECISION CO.
- ❖ Manufacturer engineer: Tony Huang
- ❖ Update date: 23/10/2024